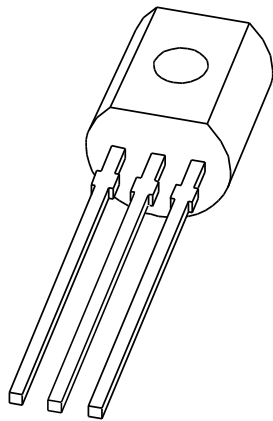


DATA SHEET



BC368

NPN medium power transistor

Product specification
Supersedes data of September 1994
File under Discrete Semiconductors, SC04

1997 Feb 28

NPN medium power transistor

BC368

FEATURES

- High current (1 A)
- Low voltage (20 V).

APPLICATIONS

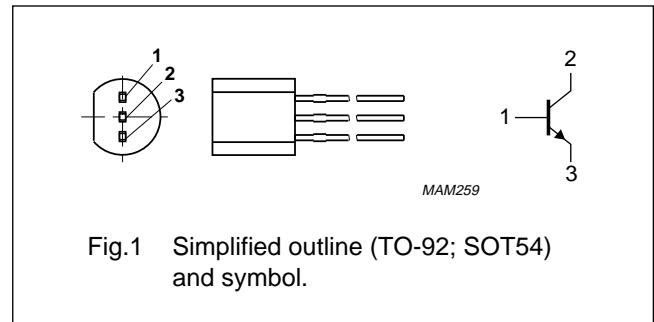
- General purpose switching and amplification
- Power applications such as audio output stages.

DESCRIPTION

NPN medium power transistor in a TO-92; SOT54 plastic package. PNP complement: BC369.

PINNING

PIN	DESCRIPTION
1	base
2	collector
3	emitter



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	32	V
V_{CEO}	collector-emitter voltage	open base	–	20	V
I_{CM}	peak collector current		–	2	A
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$	–	0.83	W
h_{FE}	DC current gain	$I_C = 500\text{ mA}; V_{CE} = 1\text{ V}$	85	375	
f_T	transition frequency	$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}; f = 100\text{ MHz}$	40	–	MHz

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	–	32	V
V _{CEO}	collector-emitter voltage	open base	–	20	V
V _{EBO}	emitter-base voltage	open collector	–	5	V
I _C	collector current (DC)		–	1	A
I _{CM}	peak collector current		–	2	A
I _{BM}	peak base current		–	200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	–	0.83	W
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	150	°C
T _{amb}	operating ambient temperature		–65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	150	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

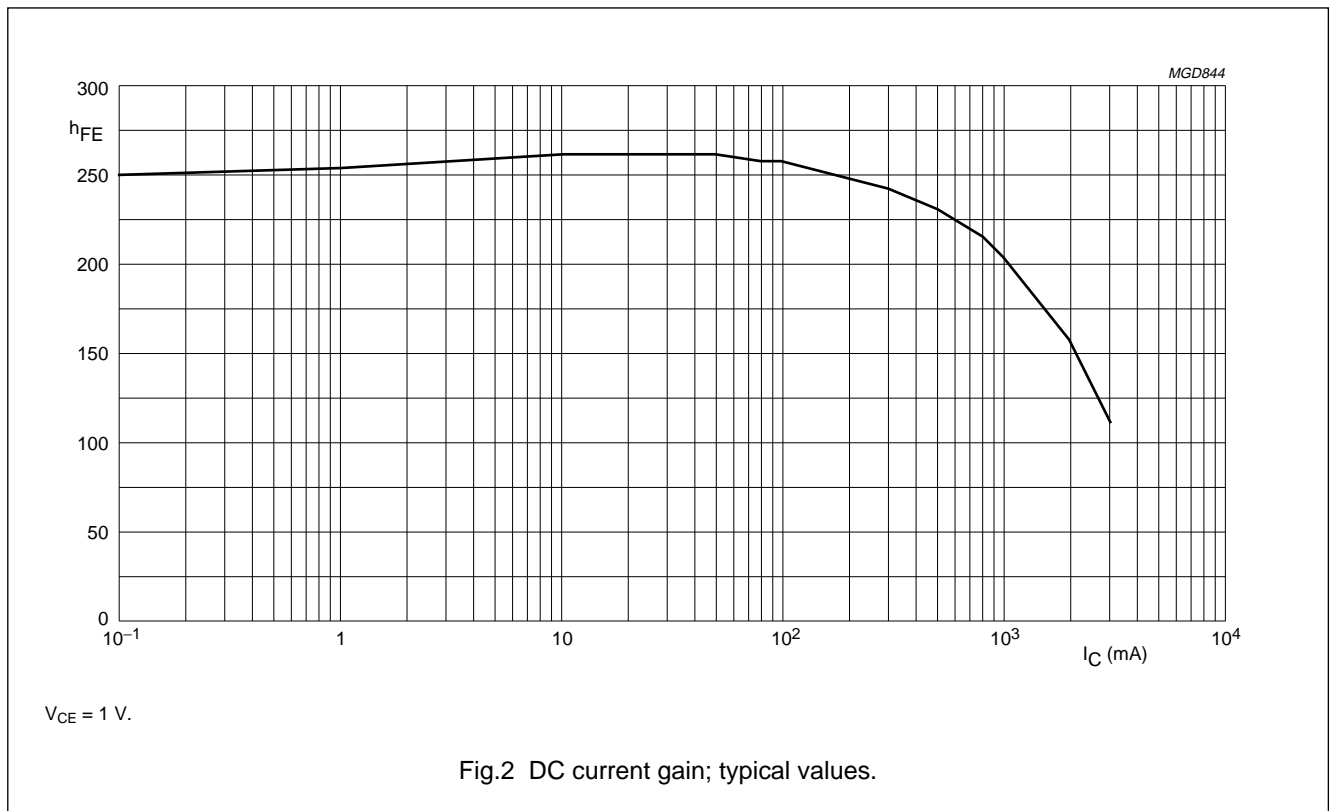
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CHARACTERISTICS

$T_j = 25\text{ }^\circ\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = 25\text{ V}$	–	100	nA
		$I_E = 0; V_{CB} = 25\text{ V}; T_j = 150\text{ }^\circ\text{C}$	–	10	μA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = 5\text{ V}$	–	100	nA
h_{FE}	DC current gain	$I_C = 5\text{ mA}; V_{CE} = 10\text{ V}$	50	–	
		$I_C = 500\text{ mA}; V_{CE} = 1\text{ V};$ see Fig.2	85	375	
		$I_C = 1\text{ A}; V_{CE} = 1\text{ V};$ see Fig.2	60	–	
h_{FE}	DC current gain BC368-16 BC368-25	$I_C = 500\text{ mA}; V_{CE} = 1\text{ V};$ see Fig.2	100	250	
			160	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 1\text{ A}; I_B = 100\text{ mA}$	–	500	mV
V_{BE}	base-emitter voltage	$I_C = 5\text{ mA}; V_{CE} = 10\text{ V}$	–	700	mV
		$I_C = 1\text{ A}; V_{CE} = 1\text{ V}$	–	1	V
f_T	transition frequency	$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}; f = 100\text{ MHz}$	40	–	MHz
$\frac{h_{FE1}}{h_{FE2}}$	DC current gain ratio of the complementary pairs	$ I_C = 500\text{ mA}; V_{CE} = 1\text{ V}$	–	1.6	



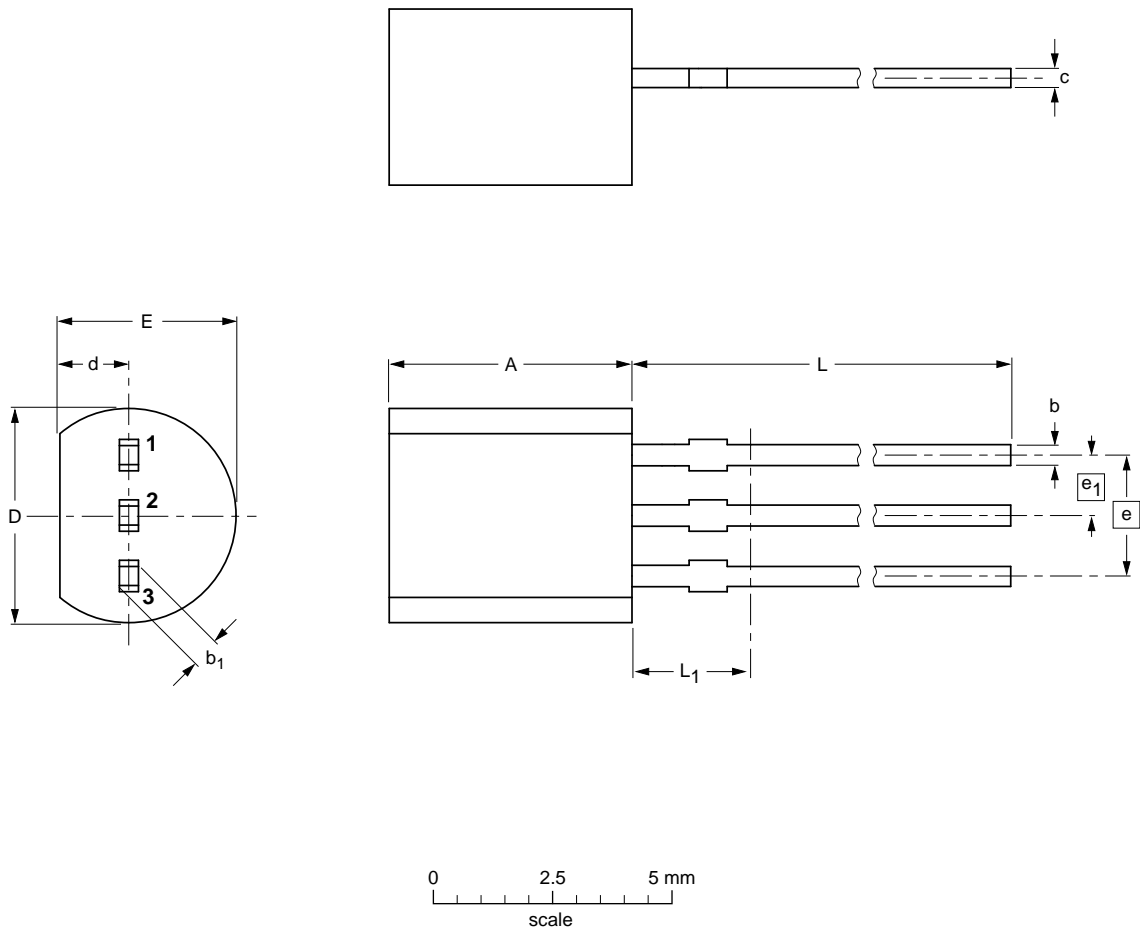
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PACKAGE OUTLINE

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



DIMENSIONS (mm are the original dimensions)

UNIT	A	b	b ₁	c	D	d	E	e	e ₁	L	L ₁ ⁽¹⁾
mm	5.2 5.0	0.48 0.40	0.66 0.56	0.45 0.40	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ		
SOT54		TO-92	SC-43		97-02-28

NPN medium power transistor

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DEFINITIONS

Data Sheet Status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

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NPN medium power transistor

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